## NSN 5962-01-352-0995



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View Online at https://aerobasegroup.com/nsn/5962-01-352-0995	
Overall Height:	
0.400 inches	
Body Length:	
1.280 inches	
Body Width:	
Between 0.220 inches and 0.310 inches	
Body Height:	
Between 0.140 inches and 0.185 inches	
Maximum Power Dissipation Rating:	
1.2 watts	
Operating Tempurature Range:	
-55.0/+125.0 degrees celsius	
Storage Tempurature Range:	
-65.0/+150.0 degrees celsius	
End Application:	
Satellite communications terminal an/usc-3 (v) 1	
Features Provided:	
Hermetically sealed and burn in and monolithic and programmed	
Inclosure Material:	
Ceramic	
Inclosure Configuration:	
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
12 input	
Case Outline Source And Designator:	
D-9 mil-m-38510	
Current Rating Per Characteristic:	
180.00 milliamperes reverse current, dc absolute	
Terminal Surface Treatment:	
Solder	
Product Name:	
Registered and-or-xor gate array	
Voltage Rating And Type Per Characteristic:	

-0.5 volts power source and 12.0 volts power source

**Time Rating Per Chacteristic:** 

25.00 nanoseconds delay

**Memory Device Type:** 

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type Ar	nd Quantity:
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24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0